Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	20	electropolishing and auxiliary adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:22
L2	4	"6176992".pn. "5677218".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 14:47
L3	2	"6685814".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 14:48
L4	2	"6001235".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 14:53
L5	270	uzoh.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 14:53
L6	212	polishing and auxiliary adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:23
L7	201	machining and auxiliary adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:22
L8	3	electromachining and auxiliary adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:22
L9	550	nicolas.xa. or nicolas.xp. and anular	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:24

L10	564	nicolas.xa. or nicolas.xp. and annular	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:24
L11	135	(nicolas.xa. or nicolas.xp.) and annular	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:28
L12	5	"677263".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:28
L13	2	"6677263".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:28
L14	2	"6277263".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:28
L15	2	"6,197,181".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:31
L16	0	(electropolishing electromachining polishing machining) and cocentric and annula	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:32
L17	4	(electropolishing electromachining polishing machining) and cocentric and annular	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:32
L18	0	(electropolishing electromachining polishing machining) and cocentric with (electrode cathode anode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:33
L19	0	(electropolishing electromachining polishing machining) and cocentric$4 with (electrode cathode anode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:33

L20	0	(electropolishing electromachining polishing machining) and cocentric$4 same (electrode cathode anode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:45
L21	26	204/228.9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:52
L22	93	204/230.7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 15:54
L23	19	204/230.7 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 16:00
L24	0	204/FOR925 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 16:01
L25	0	204/FOR925	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 16:01
L26	0	204/925	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 16:02
L27	0	205/460 and auxiliary adj electrode with annular	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 16:02
L28	0	205/460 and auxiliary adj electrode with (ring annular)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 16:02
L29	1	204/230.7 and auxiliary adj electrode with (ring annular)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 16:09

L30	62	electropolish$3 with electrodeposit$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 16:09
L31	23	30 with (semiconductor silicon wafer substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 17:04
L32	85	end adj point adj detection with current	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:12
L33	172	end adj point adj detection with thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:12
L34	298	end adj point adj detection with optical	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:13
L35	74	end adj point adj detection with current and (semiconductor silicon wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:13
L36	165	end adj point adj detection with thickness and (semiconductor silicon wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:14
L37	271	end adj point adj detection with optical and (semiconductor silicon wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:15
L38	515	mesh adj (anode cathodes electrodes) and (electropolish$3 electromachin$3 polish$3 machin$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:19
L39	742416	annular adjmesh adj (anode cathodes electrodes) and (electropolish$3 electromachin$3 polish$3 machin$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:19

L40	0	annular adj mesh adj (anode cathodes electrodes) and (electropolish$3 electromachin$3 polish$3 machin$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:20
L41	2	annular with mesh adj (anode cathodes electrodes) and (electropolish$3 electromachin$3 polish$3 machin$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:20
L42	29	annular with mesh with (anode cathodes electrodes) and (electropolish$3 electromachin$3 polish$3 machin$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:21
L43	58	ring with mesh with (anode cathodes electrodes) and (electropolish$3 electromachin$3 polish$3 machin$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:23
L44	515	mesh adj (anode cathodes electrodes) and (electropolish$3 electromachin$3 polish$3 machin$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:23
L45	197	mesh adj (anode cathodes electrodes) and (electropolish$3 electromachin$3 polish$3 machin$3) and ("204"/$5 "205"/$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 18:37
L46	2	"6802946".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/02 19:29